

N-channel TrenchMOS logic level FET Rev. 03 — 4 June 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

Suitable for logic level gate drive sources

Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference	data					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	75	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>		-	3.5	4.2	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C		-	3.1	3.7	mΩ
Avalanch	e ruggedness						

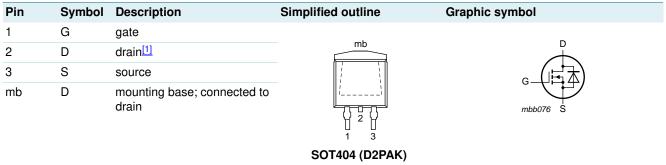
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Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50 \ \Omega; \ V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 \ ^\circ\text{C}; \ unclamped \end{split} $	-	-	1.2	J
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 44 V; T_j = 25 °C;$ see <u>Figure 13</u>	-	37	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information



[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK964R2-55B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V _{GS}	gate-source voltage			-15	-	15	V
	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 3}}{\text{Figure 1}};$ see $\frac{\text{Figure 1}}{1}$	<u>[1]</u>	-	-	75	Α
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	[1]	-	-	75	А
		T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	-	191	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u>		-	-	765	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	diode						
ls	source current	T _{mb} = 25 °C	<u>[1]</u>	-	-	75	А
			[3]	-	-	191	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	765	А
Avalanche ru	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(\text{init})} = 25 \ ^\circ\text{C}; \ \text{unclamped} \end{array}$		-	-	1.2	J

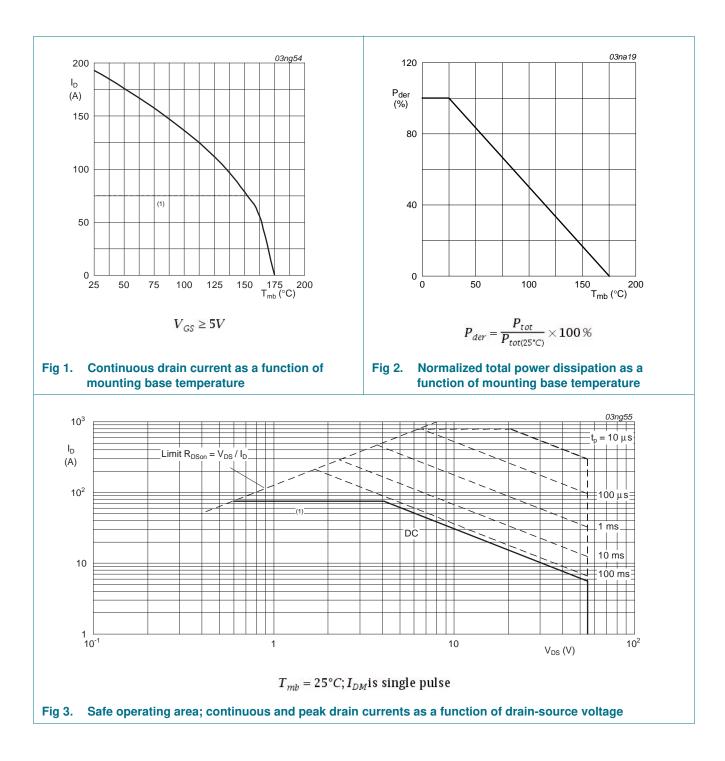
[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

[3] Current is limited by power dissipation chip rating.

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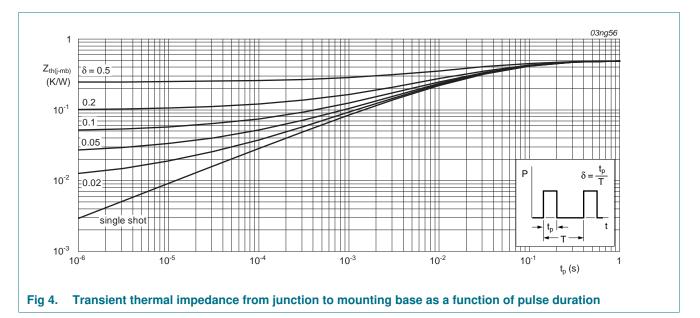
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <mark>Figure 4</mark>	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed circuit-board	-	50	-	K/W



6. Characteristics

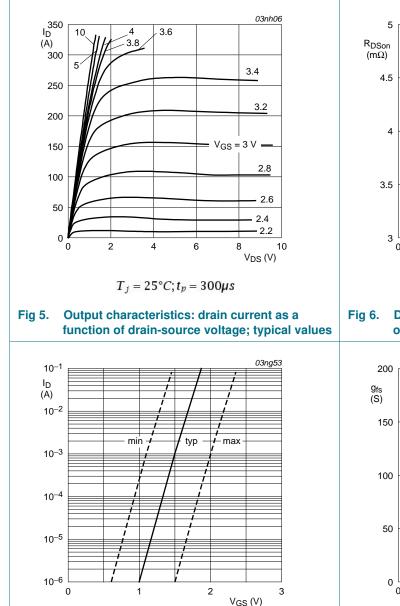
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{V}; \text{T}_\text{j} = 25 ^\circ\text{C}$	55	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	1.1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 15 V; T _j = 25 °C	-	2	100	nA
		$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = -15 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
R _{DSon} drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	3.5	4.2	mΩ	
		V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	4.4	mΩ
	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	8.4	mΩ	
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	3.1	3.7	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$	-	95	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	17	-	nC
Q _{GD}	gate-drain charge		-	37	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	7665	10220	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	1044	1253	pF
C _{rss}	reverse transfer capacitance		-	466	638	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	63	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	232	-	ns
t _{d(off)}	turn-off delay time		-	273	-	ns
t _f	fall time		-	178	-	ns
L _D internal drain inductance		from upper edge of drain mounting base to centre of die SOT404 ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_i = 25 ^\circ\text{C}$	-	7.5	-	nH

Source-drain diode

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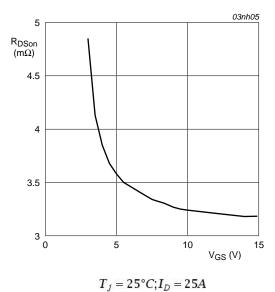
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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{SD}	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^\circ\text{C}; \\ \text{see } \underline{\text{Figure 15}}$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s;$	-	78	-	ns
Qr	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	171	-	nC

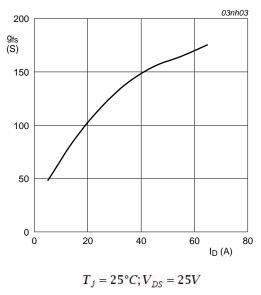


 $T_{j} = 25 \,^{\circ}C; V_{DS} = V_{GS}$





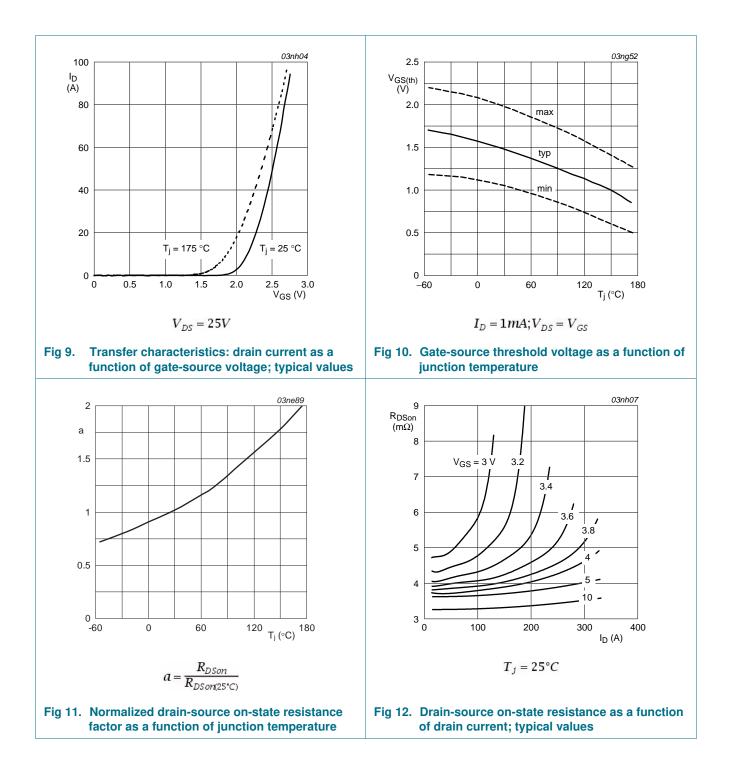






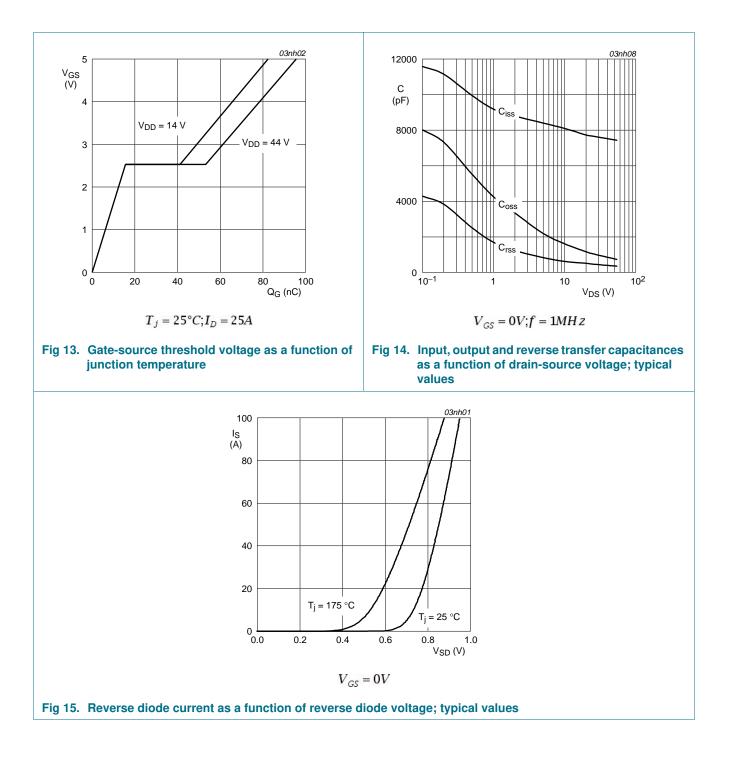
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7. Package outline

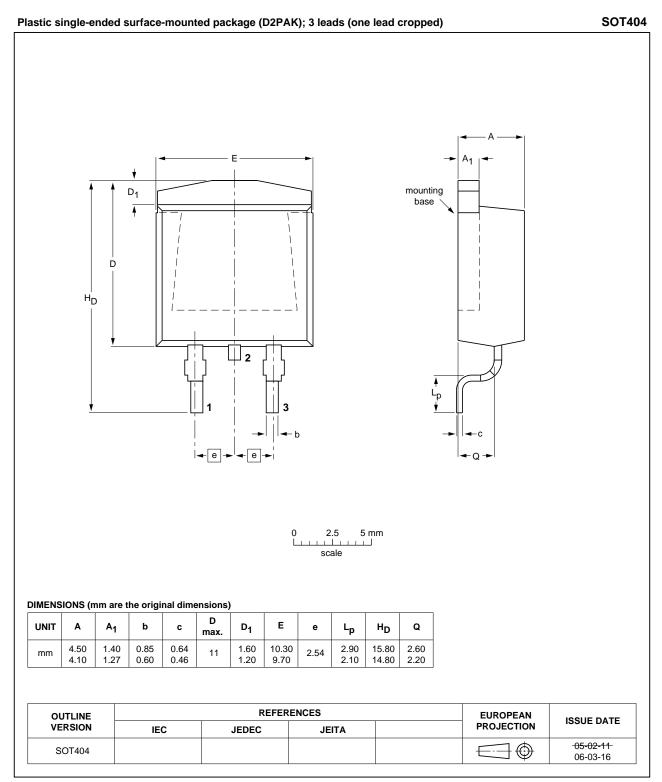


Fig 16. Package outline SOT404 (D2PAK)

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BUK964R2-55B

8. Revision history

Table 7.Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK964R2-55B v.3	20100604	Product data sheet	-	BUK95_964R2_55B-02
Modifications:		of this data sheet has bee niconductors.	n redesigned to comply w	ith the new identity guidelines
	 Legal texts 	have been adapted to the	e new company name wh	ere appropriate.
	Type number	er BUK964R2-55B separa	ated from data sheet BUK	(95_964R2_55B-02.
BUK95_964R2_55B-02 (9397 750 10277)	20021008	Product data	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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